



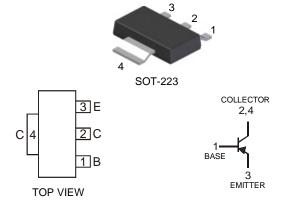


Features

- **Epitaxial Planar Die Construction**
- Complementary NPN Type Available (DZT2222A)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Amplification and Switching
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

Mechanical Data

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking & Type Code Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.115 grams (approximate)



Schematic and Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Continuous Current (Note 3)	Ic	-600	mA
Peak Collector Current	I _{CM}	-800	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Dower Dissipation @ T 259C	D	1000 (Note 3)	- mW	
Power Dissipation @ T _A = 25°C	P _d	1500 (Note 4)		
Power Derating Factor above 25°C (Note 4)	P _{der}	12	mW/°C	
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C	
Thermal Resistance, Junction to Ambient Air @ T _A = 25°C (Note 4)	$R_{ hetaJA}$	83.3	°C/W	

Notes:

- No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- Device mounted on 2" x 2" FR-4 PC board, 2 oz. copper, single sided, pad layout as shown on page 4, or on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- Device mounted on FR-4 PCB, 7cm² of copper pad area.



Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Conditions	
OFF CHARACTERISTICS (Note 5)						
Collector-Base Cutoff Current	I _{CBO}		-0.01		$V_{CB} = -50V, I_{E} = 0$	
			-10	μΑ	$V_{CB} = -50V$, $I_E = 0$, $T_A = 150^{\circ}C$	
Collector Cutoff Current	I _{CEX}	_	-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -0.5V$	
Base Cutoff Current	I_{BL}		-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -0.5V$	
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-60	_	V	$I_C = -10 \mu A, I_E = 0$	
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-60	_	V	$I_C = -10 \text{ mA}, I_B = 0$	
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5	_	V	$I_E = -10 \mu A, I_C = 0$	
ON CHARACTERISTICS (Note 5)					_	
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	-0.4	V	$I_C = -150 \text{mA}, I_B = -15 \text{mA}$	
Concetor Emitter Cataration Voltage	VCE(SAT)		-1.6	V	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$	
		75	_		$V_{CE} = -10V, I_{C} = -100\mu A$	
	h _{FE}	100	_		$V_{CE} = -10V, I_{C} = -1mA$	
DC Current Gain		100	_		$V_{CE} = -10V, I_{C} = -10mA$	
		100	300	_	$V_{CE} = -10V, I_{C} = -150mA$	
		50	_		$V_{CE} = -10V, I_{C} = -500mA$	
Base-Emitter Saturation Voltage	V _{BE(SAT)}		-1.3	V	$I_C = -150 \text{mA}, I_B = -15 \text{mA}$	
ŭ		_	-2.6	V	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$	
SMALL SIGNAL CHARACTERISTICS	Ī					
Current Gain-Bandwidth Product	f _T	200	_	MHz	$V_{CE} = -20V, I_{C} = -50mA, f = 100MHz$	
Output Capacitance	C _{obo}	_	8	pF	$V_{CB} = -10V$, $I_E = 0A$, $f = 1MHz$	
Input Capacitance	C_{ibo}	_	30	pF	$V_{EB} = -2V$, $I_C = 0A$, $f = 1MHz$	
SWITCHING CHARACTERISTICS	SWITCHING CHARACTERISTICS					
Turn-On Time	t _{on}	_	45	ns		
Delay Time	t _d	_	10	ns	$V_{CC} = -30V, I_{C} = -150mA, I_{B1} = -15mA$	
Rise Time	t _r	_	40	ns		
Turn-Off Time	t _{off}	_	100	ns	V _{CC} = -6V, I _C = -150mA, I _{B1} = I _{B2} = -15mA	
Storage Time	ts		80	ns		
Fall Time	t _f	_	30	ns		

5. Pulse Test: Pulse width, tp<300 uS, Duty Cycle, d< =0.02 Notes:

Typical Characteristics @T_A = 25°C unless otherwise specified

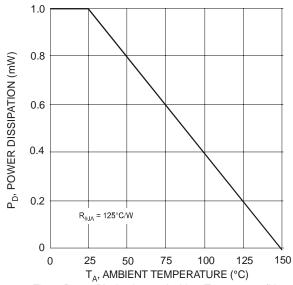
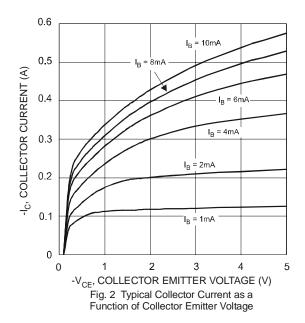


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)





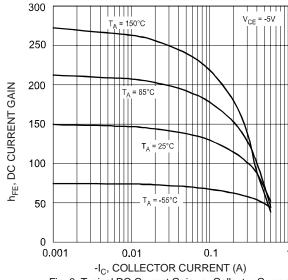
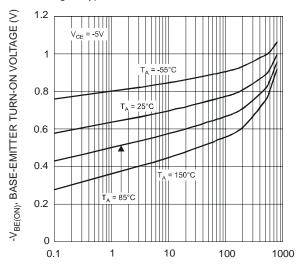
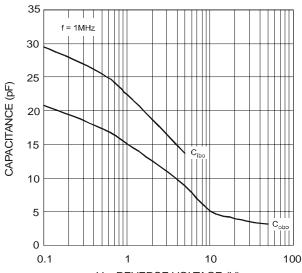


Fig. 3 Typical DC Current Gain vs. Collector Current



-I_C, COLLECTOR CURRENT (mA) Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current



V_R, REVERSE VOLTAGE (V) Fig. 7 Typical Capacitance Characteristics

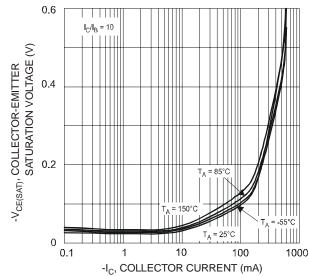
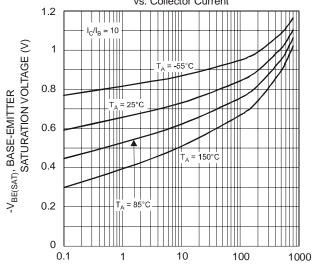


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current



 $-I_{\mathbb{C}}$, COLLECTOR CURRENT (mA) Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

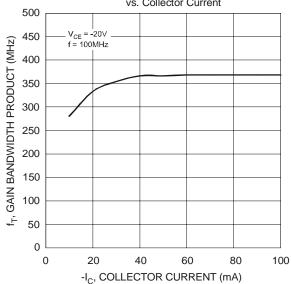


Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current



Ordering Information (Note 6)

Device		Packaging	Shipping	
	DZT2907A-13	SOT-223	2500/Tape & Reel	

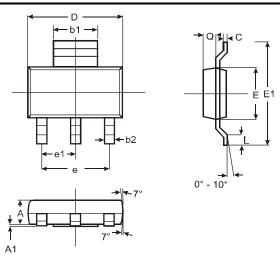
Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



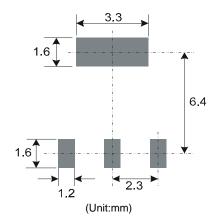
OH = Manufacturer's code marking K2F = Product type marking code YWW = Date code marking Y = Last digit of year ex: 7 = 2007 WW = Week code 01 - 52

Package Outline Dimensions



SOT-223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b1	2.90	3.10	3.00		
b2	0.60	0.80	0.70		
C	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	_	_	4.60		
e1	_		2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout: (Based on IPC-SM-782)



IMPORTANT NOTICE

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